

VERSION WITH MARKINGS TO SHOW CHANGES MADE

3. (amended) The method for producing a silicon single crystal ingot according to Claim 1[ or Claim 2], characterized in that said conditions (a) and (b) are adjusted by changing the pulling speed of the silicon single crystal ingot when the silicon single crystal ingot is produced by the Czochralski method.

4. (amended) A silicon single crystal wafer with decreased grown-in defects, which is obtained from said silicon single crystal ingot according to [one of] Claim[s] 1[ to 3].

5. (amended) A silicon perfect single crystal wafer free from grown-in defects, which is obtained from said silicon single crystal ingot according to [one of] Claim[s] 1[ to 3].

23. (amended) The CZ method-based single crystal ingot production device according to [one of Claims 17 to 21] Claim 17, characterized in that said single crystal ingot is a single crystal ingot, including a portion of a perfect crystal.